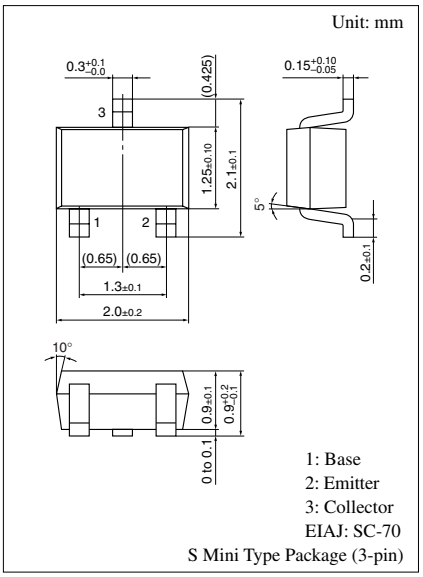
2SA2028

Silicon PNP epitaxial planer type

For DC-DC converter



Marking Symbol: AT

■ Features

- Large current capacitance
- Low collector to emitter saturation voltage
- High-speed switching
- Small type package, allowing downsizing and thinning of the equipment.

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	−20	V
Collector to emitter voltage	V_{CEO}	−20	V
Emitter to base voltage	V_{EBO}	−5	V
Peak collector current	I_{CP}	−3	A
Collector current	I_C	−1	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector to base voltage	V_{CBO}	$I_C = -10$ μA, $I_E = 0$	−20			V
Collector to emitter voltage	V_{CEO}	$I_C = -1$ mA, $I_B = 0$	−20			V
Emitter to base voltage	V_{EBO}	$I_E = -10$ μA, , $I_C = 0$	−5			V
Forward current transfer ratio *	h_{FE}	$V_{CE} = -2$ V, $I_C = -100$ mA	160		560	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -200$ mA, $I_B = -10$ mA		−40	−100	mV
Collector output capacitance	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		20	30	pF
Transition frequency	f_T	$V_{CB} = -10$ V, $I_E = 10$ mA f=200 MHz		170		MHz